

Impact of defect layers on superconductivity in Bi-O-S compounds

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Newly discovered Bi-S-O compounds remain an enigma in attempts to understand their electronic properties. Recent study of $\text{Bi}_4\text{O}_4\text{S}_3$ has shown it to be a mixture of two phases, Bi_2OS_2 and $\text{Bi}_3\text{O}_2\text{S}_3$, the latter being superconducting. Using density functional theory, we explore the electronic structure of both the phases and the effect of the introduction of stacking faults. Our results demonstrate the S_2 layers dope the BiS_2 bands, these electrons are accumulated in the BiS planes. We show the introduction of defects in the stacking diminishes the doping which would suppress superconductivity.

The recent discovery of superconductivity in two new compounds, $\text{Bi}_4\text{O}_4\text{S}_3$ [1–4] and $\text{LaO}_x\text{F}_{1-x}\text{BiS}_2$ [5–8], has raised great interest. In fact it is a whole new class of superconductors that has been unveiled, as a number of BiS_2 -based compounds exhibit superconductivity. All those compounds share the same structure : a stacking of alternating BiS_2 and spacer layers. Superconductivity is thought to arise from doping of the BiS_2 layers. Both hole, $\text{Sr}_{1-x}\text{La}_x\text{FBiS}_2$ [9], and electron, $\text{La}_{1-x}\text{M}_x\text{OBiS}_2$ ($\text{M} = \text{Ti}, \text{Zr}, \text{Hf}, \text{Th}$) [10], doping result in superconductivity. The versatility of the $\text{La}(\text{O},\text{F})\text{BiS}_2$ system has been demonstrated by replacement of La with a range of lanthanide Ln^{3+} ions [11–15]— a maximum T_c of 10.6 K is reported in $\text{LaO}_x\text{F}_{1-x}\text{BiS}_2$ for $x = 0.5$. However given the absence of a systematic study and the difficulties with sample preparation, it may still be possible that improvement in condition and control of disorder might result in achieving higher temperature superconductivity.

Electronic structure calculations have mainly focused on the $\text{LaO}_x\text{F}_{1-x}\text{BiS}_2$ ($x = 0, 0.5$) materials partially due to uncertainties in the composition of the Bi-O-S superconducting phase. These calculations indicated that the superconducting electrons are a mixture of Bismuth $6p$ and Sulphur $3p$ states [16, 17]. Electronic and thermodynamic properties of this group of materials are indeed exciting and enigmatic and suggestions range from spin fluctuations mediated superconductivity [18] to proximity to ferroelectricity and Charge Density Waves (CDW) instability [19].

Despite the excitement, doubts still remain concerning the structure of the first superconductor, $\text{Bi}_4\text{O}_4\text{S}_3$. However Phelan et al. just published an extensive study of the chemistry of these compounds and concluded that $\text{Bi}_4\text{O}_4\text{S}_3$ was actually a two-phased material [20]. The two phases are Bi_2OS_2 and $\text{Bi}_3\text{O}_2\text{S}_3$, the later being likely the superconducting one.

Composed of BiS_2 , S_2 and Bi_2O_2 layers, the latter being a spacer layer (Figure 1), $\text{Bi}_3\text{O}_2\text{S}_3$ is made of alternating BiS_2 and S_2 layers, all separated by spacer layers, whereas in Bi_2OS_2 only the two BiS_2 layers are present. Initial experimental results suggest that superconductivity is suppressed by the inclusion of additional BiS_2 layers disrupting the alternate of S_2 and BiS_2 sheets. Stacking faults play a significant role in superconducting properties of several families of materials [21]. For example, changes to the ground state have been observed in the presence of stacking faults in other systems, including modifications to superconductivity [22, 23].

In this paper we explore the electronic structure of the superconducting and non-superconducting phases of the Bi-O-S compounds. The role of introducing additional BiS_2 layers in the superconductor $\text{Bi}_3\text{O}_2\text{S}_3$ is also investigated. Like in the $\text{La}(\text{O},\text{F})\text{BiS}_2$ systems we find that the BiS_2 layers play a critical role in superconductivity. Our analysis indicates that the S_2 sheets donate significant electron density to the BiS_2 bands. Those electrons are localised within BiS planes rather than through the BiS_2 sheets. Interruption of the BiS_2 , S_2 stacking sequence in defect structures is shown to reduce electron donation to the BiS planes, suppressing superconductivity.

Band structures and density of states for Bi_2OS_2 and $\text{Bi}_3\text{O}_2\text{S}_3$ were calculated, using the SIESTA code [24, 25], implementing the generalized gradient approximation in the shape of the Perdew, Burke, and Ernzerhof functional. It uses non-conserving pseudopotentials to replace the core electrons, while the valence electrons are described using atomic-like orbitals as basis states at the double zeta polarized level. In the case of the two known structures, experimentally determined structural parameters were used in our calculations [20][28]. Spin polarized calculations were found to be unnecessary.

In order to simulate how stacking faults perturb the electronic structure, we investigated materials where the relative number of BiS_2 and S_2 layers was changed. In $\text{Bi}_3\text{O}_2\text{S}_3$, the stacking is $2 \times \text{BiS}_2 / \text{Bi}_2\text{O}_2 / \text{S}_2 / \text{Bi}_2\text{O}_2 / 2 \times \text{BiS}_2 / \text{Bi}_2\text{O}_2 / \text{S}_2 / \text{Bi}_2\text{O}_2$ (Figure 1). The sequence is repeated twice because of symmetry : S_2 layers

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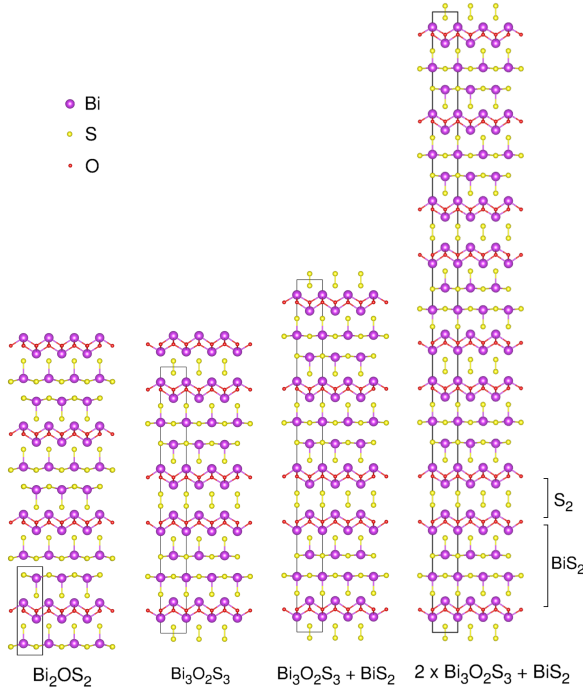


FIG. 1: Crystal structure of Bi_2OS_2 , $\text{Bi}_3\text{O}_2\text{S}_3$, $\text{Bi}_3\text{O}_2\text{S}_3$ with an added stacking fault, and two $\text{Bi}_3\text{O}_2\text{S}_3$ on top of each other with an added stacking fault, represented in Vesta [26]. They are formed of a stacking of BiS_2 , S_2 and Bi_2O_2 layers, the latter being a spacer layer. These structures implement four different S_2/BiS_2 ratios : 0, 1, $2/3$, $4/5$, i.e. four different frequencies of occurrence of stacking faults.

shift the spacer blocks, and thus double the unit cell volume. To modify the ratio, we added a BiS_2 layer, with its corresponding spacer layer, at the top of $\text{Bi}_3\text{O}_2\text{S}_3$. We therefore obtain the following stacking : $2 \times \text{BiS}_2 / \text{Bi}_2\text{O}_2 / \text{S}_2 / \text{Bi}_2\text{O}_2 / 2 \times \text{BiS}_2 / \text{Bi}_2\text{O}_2 / \text{S}_2 / \text{Bi}_2\text{O}_2 / 2 \times \text{BiS}_2 / \text{Bi}_2\text{O}_2$. This can be done because BiS_2 layers, unlike S_2 , do not shift spacer blocks. The piling up of unit cells is therefore not disturbed by the added block. Similarly we also constructed a structure in which an additional BiS_2 every two units cells was included. In total, we calculated the electronic structure of compounds with four different S_2/BiS_2 ratios : 0, 1, $2/3$ and $4/5$. The structure of BiS_2 layers is different in Bi_2OS_2 and $\text{Bi}_3\text{O}_2\text{S}_3$, the most noticeable difference being the angle between Bismuth and Sulphur atoms in the BiS planes, which is larger in the parent phase. We did calculations for both, and the results being extremely similar (e.g. less than 0.1 eV difference for the height of bands), we decided to show the results for $\text{Bi}_3\text{O}_2\text{S}_3$'s BiS_2 layers, as the stacking faults appear in this compound.

Bi_2OS_2 and $\text{Bi}_3\text{O}_2\text{S}_3$ only differ by the replacement in the second compound of one out of two BiS_2 layer by an S_2 layer. In terms of stoichiometry, as noted by Phelan et al. [20], Bi_2OS_2 can be written BiOBiS_2 , just as

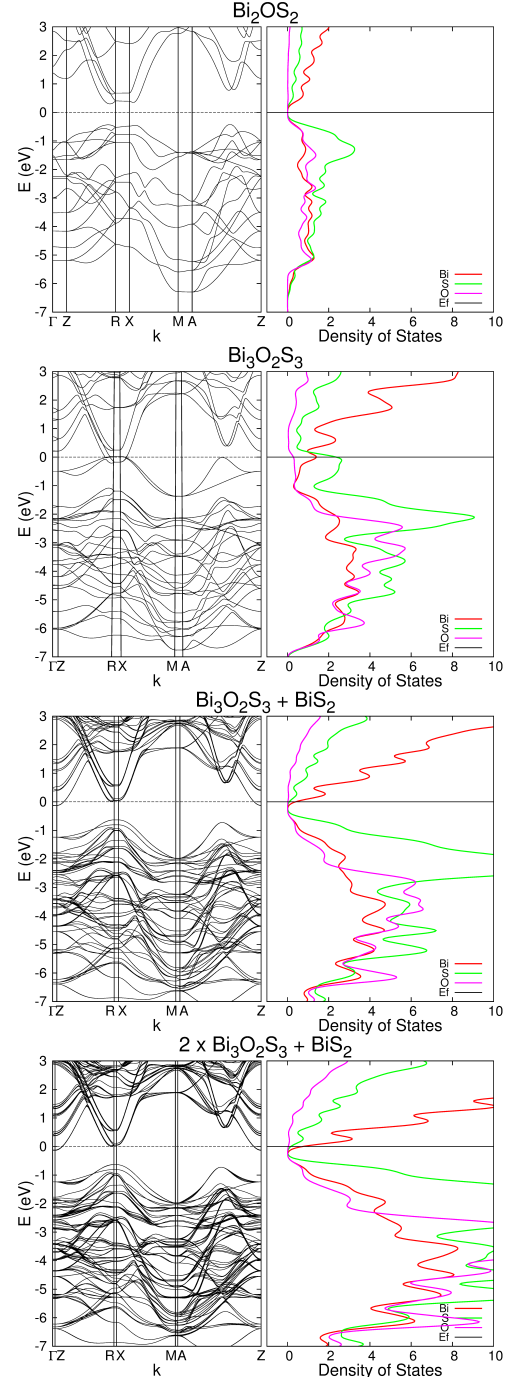


FIG. 2: Band structures and density of states for the four simulated compounds. From top to bottom, they correspond to the structures from left to right in Figure 1. The two last compounds are simulations of stacking faults at two different frequencies in $\text{Bi}_3\text{O}_2\text{S}_3$.

the parent phase of the Lanthanum compound, LaOBiS_2 . The band structure of Bi_2OS_2 has features close to the Fermi energy which are similar to the undoped LaOBiS_2 phase. Of specific interest is the set of Bismuth $6p$ and Sulphur $3p$ bands that are found in all the band struc-

tures calculated (Figure 2). Further partial density of states calculations enabled us to confirm that exact composition. In the first case, Bi_2OS_2 , they are just above the Fermi level, at around 0.3 eV at their minimum. This is very close to the corresponding minimum in LaOBiS_2 (0.2 eV). The gap is 0.7 eV wide, twice as large as in the LaOBiS_2 case (0.37 eV).

In $\text{Bi}_3\text{O}_2\text{S}_3$, one of these bands is crossing the Fermi level, near the R and X points, just as in $\text{LaO}_{0.5}\text{F}_{0.5}\text{BiS}_2$. At these points it interacts with two other bands. These are in great majority composed of S 3*p* states, as the density of states shows. They are not present in the parent phase, Bi_2OS_2 , which means they come from the S_2 layer. To confirm this assignment, we plotted the local density of states in real space, for the range of energies between -1.5 eV and 0 eV (Figure 3). This range contains the bands we are interested in, with almost nothing else in. The results are quite clear : it is indeed the S_2 layer that gathers all the electron density. Moreover, this density is organised as a torus oriented along the *z* axis around each S atom. The fact that the density decreases near the atom comes from the pseudopotentials, but we do learn that the orbitals lying at or just above the Fermi level correspond mainly to p_x, p_y electrons on the S_2 dimers (oriented along *z*). The concentration of the electron density on the atoms rather than on the S-S bond could be indicative of a weakening of the S-S interaction. Indeed, the simulation indicates there is a repulsive force of 5.5 eV/Å for each of these atoms, along the S-S bond.

We also plotted the local density of states in real space for the range of energies between 0 eV and 1.5 eV (Figure 3). This range contains the characteristic bands present in all the BiS_2 -based compounds. We can clearly see that the charges are localised in the BiS_2 layer, more precisely in the two BiS planes. Indeed the S atoms in the BiS_2 layer but outside the BiS planes gather as many electrons in that range of energy as the S atoms in the S_2 layer.

The electronic structure of $\text{Bi}_3\text{O}_2\text{S}_3$ with an added stacking fault does not differ a lot from $\text{Bi}_3\text{O}_2\text{S}_3$'s (Figure 2). However three things do change : the height of the Fermi level, of the S_2 bands, and the BiS bands around Γ . The S_2 bands are much closer to the lower bands, while the energy difference between BiS bands and the lower bands is preserved. A gap appears, of about 0.6 eV, between these two sets of bands. The Fermi level is lower, the S_2 bands not raising it as much as in $\text{Bi}_3\text{O}_2\text{S}_3$. In consequence, the characteristic BiS bands around R and X do not cross the Fermi level. But they do cross it around Γ , the bands being lower there than at R or X, unlike any BiS_2 compound encountered so far. The band structure of $\text{Bi}_3\text{O}_2\text{S}_3$ with one stacking fault every two unit cell is similar. The only differences visible are in the density of states, well above or under the Fermi level. The height of the S_2 and BiS bands does not seem to be affected.

The key result of this study is the fact that, in spite of it being a nominally stoichiometric composition (no dop-

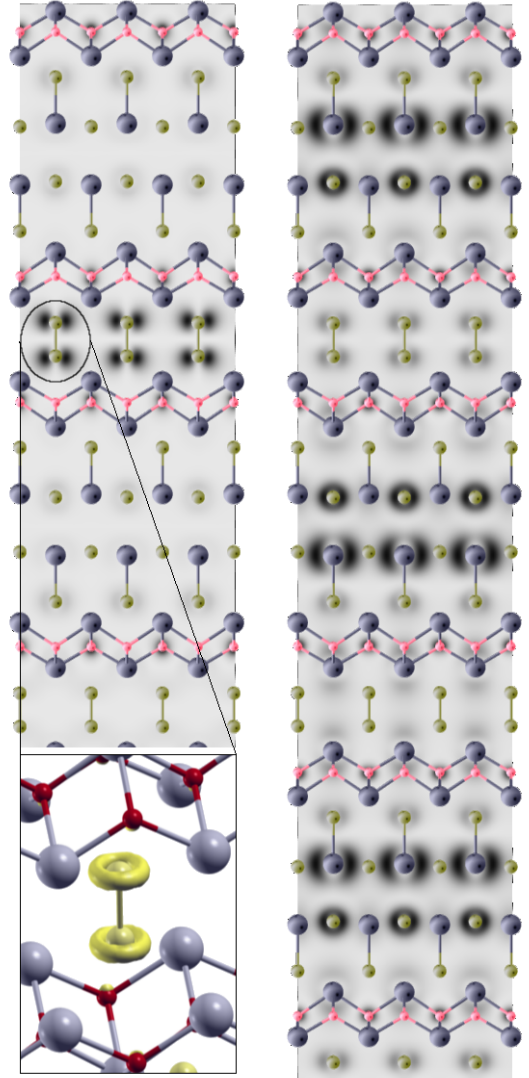


FIG. 3: Local density of states of $\text{Bi}_3\text{O}_2\text{S}_3$ in real space for energies in $[-1.5, 0]$ (left) and $[0, 1.5]$ (right), plotted with XCrySDen [27]. Framed is a 3D plot of an isosurface centred on the S-S dimer. In the first case, the S_2 layer gathers most of the density. In the second case it is the BiS planes, without the extra S atoms, that gather the density. Half of the atoms represented are not in the plane corresponding to the density plot.

ing), the S_2 layers in the $\text{Bi}_3\text{O}_2\text{S}_3$ compound act as effective dopants of the parent, insulating compound. They push a p_x, p_y -like band of the S_2 layer onto the bottom of the conduction band, thereby transferring part of the electrons of the S_2 dimers to the BiS_2 plane. Although the actual band energies are not quantitatively accurate (the quasi-particle gap would be larger than the GGA band gap, on one hand, but the spin-orbit coupling would

push down one of the BiS_2 related conduction bands, on the other) the qualitative fact remains, in agreement with experiment. Indeed, the results of our calculations are in agreement with the observed metallic behaviour of $\text{Bi}_3\text{O}_2\text{S}_3$ [20]. Furthermore, the experimental observation of an anomalously short S-S distance in the S_2 layers is also consistent with electron depletion of the S_2 layer. Indeed, a substantial residual force of 5.5 eV/Å is observed for the S atoms in the S_2 layer in the direction of elongating the distance, which suggests a larger depletion than the one obtained in the calculations.

The link between superconductivity and the crossing of BiS_2 bands is supported by the evolution of superconductivity and of band structure with stacking faults. The latter lower the S_2 bands, causing these bands not to cross the Fermi level. Everything points towards this lowering being responsible for the loss of superconductivity when stacking faults become numerous.

As the band structures of the two compounds containing stacking faults are virtually inseparable around the Fermi level, we can infer that their influence decreases slowly with its frequency of appearance. This is in apparent contradiction with the fact that superconductivity has been reported in a compound having around 20% of Bi_2OS_2 -like stacking, equivalent to the $\text{S}_2/\text{BiS}_2 = 4/5$ ratio we simulated [20]. But when looking at the corresponding TEM data, one can see that the stacking faults are gathered together. The magnetization measurement shows the superconducting volume of the compound is divided by two when the Bi_2OS_2 -like stacking goes from <10% to 20%. Therefore it is reasonable to postulate

that the non-superconducting phase is a volume surrounding the Bi_2OS_2 -like stacking. As a consequence, $\text{Bi}_3\text{O}_2\text{S}_3$ is extremely sensitive to this type of disorder. Further refinement of purity and crystal growth combined with electronic structure measurements and measurements under pressure are required to provide further insight into both normal and superconducting states of these fascinating materials.

Finally, the calculations of density of states in real space indicate that the BiS_2 bands, seeming to be central for superconductivity in these compounds, actually come from the BiS planes. Therefore finding other structures having such planes could be very interesting in order to tune their interactions differently, and maybe transform their behaviour.

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- [28] For the first phase, Bi_2OS_2 , the space group is $P4/nmm$, and the lattice parameters are $a = 3.9661 \text{ \AA}$ and $c = 13.798 \text{ \AA}$. The atoms coordinates are $\text{Bi1} : (0.25, 0.25, 0.59122)$, $\text{Bi2} : (0.25, 0.25, 0.12989)$, $\text{O} : (0.75, 0.25, 0.5)$, $\text{S1} : (0.25, 0.25, 0.328)$, $\text{S2} : (0.25, 0.25, 0.9063)$. For the second phase, $\text{Bi}_3\text{O}_2\text{S}_3$, the space group is $I4/mmm$, and the lattice parameters are $a = 3.96721 \text{ \AA}$ and $c = 41.2847 \text{ \AA}$. The atoms coordinates are $\text{Bi}_1 : (0, 0, 0.05699)$, $\text{Bi}_2 : (0, 0, 0.20865)$, $\text{Bi}_3 : (0, 0, 0.38245)$, $\text{O} : (0, 0.5, 0.0852)$, $\text{S}_1 : (0, 0, 0.14595)$, $\text{S}_2 : (0, 0, 0.2870)$, $\text{S}_3 : (0, 0, 0.47748)$. All the occupancies are equal to one.